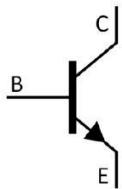


Silicon NPN transistor in a TO-220 Plastic Package.

High voltage.

High voltage switching and humidifier.

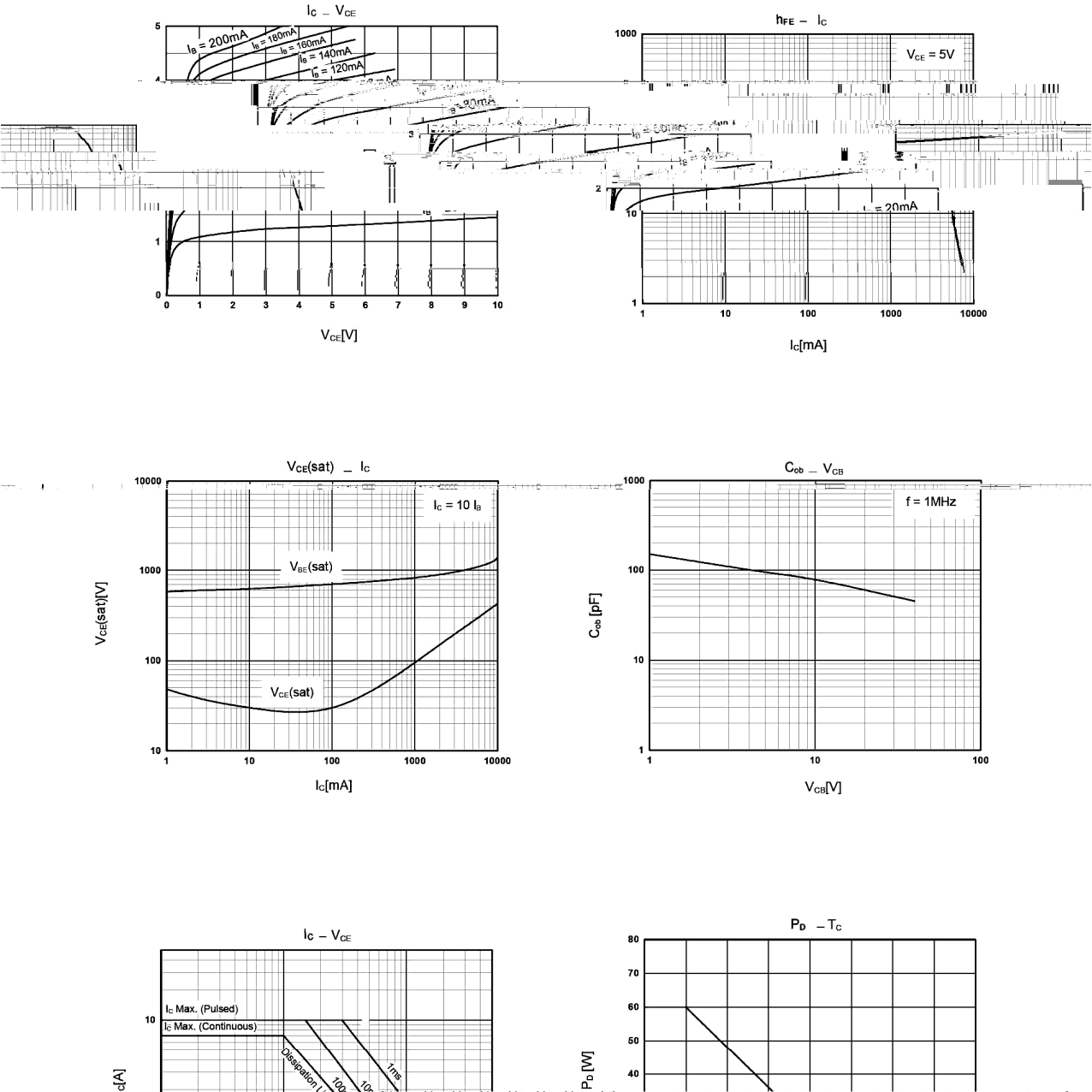


PIN1 Base PIN 2 Collector PIN 3 Emitter

See Marking Instructions.

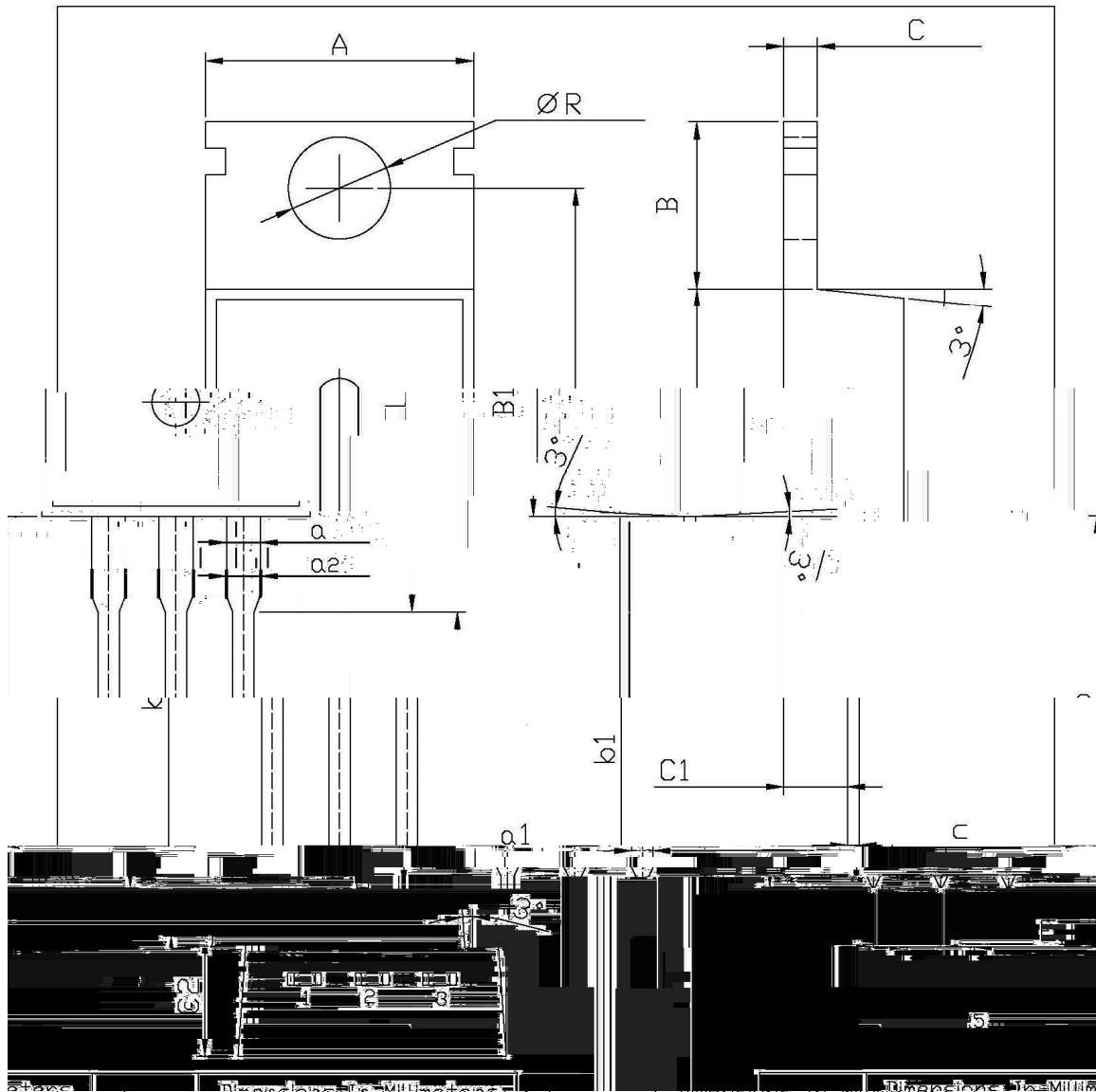
Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	400	V
Collector to Emitter Voltage	V_{CEO}	200	V
Emitter to Base Voltage	V_{EBO}	6.0	V
Collector Current(DC)	I_C	7.0	A
Collector Current(Pulse)	I_{CP}	10	A
Base Current	I_B	4.0	A
Collector Dissipation	P_C	60	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55~150	

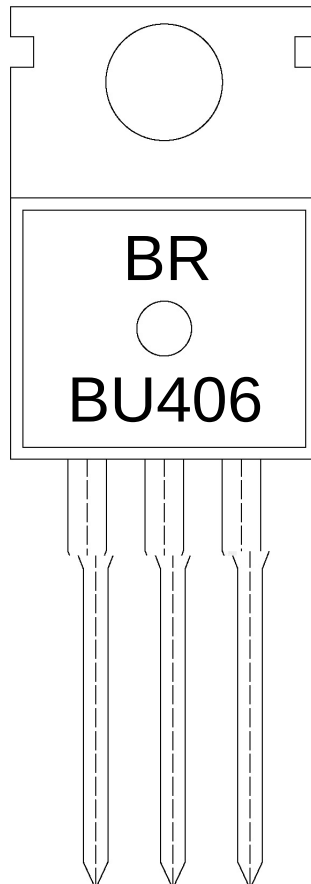
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector Cut-Off Current	I_{CBO}	$V_{CB}=400V$ $I_E=0$			10	μA
Collector Cut-Off Current	I_{CEO}	$V_{CE}=200V$ $I_B=0$			50	μA
Emitter Cut-Off Current	I_{EBO}	$V_{BE}=6.0V$ $I_C=0$			10	μA
Collector Cut-Off Current	$I_{CES(1)}$	$V_{CE}=400V$ $V_{BE}=0$			5	mA
	$I_{CES(2)}$	$V_{CE}=250V$ $V_{BE}=0$			100	μA
	$I_{CES(3)}$	$V_{CE}=250V$ $V_{BE}=0$ $T_C=150$			1.0	mA
DC Current Gain	h_{FE}	$V_{CE}=5.0V$ $I_C=2.0A$	60		120	
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=5.0A$ $I_B=0.5A$			1.0	V
Base to Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C=5.0A$ $I_B=0.5A$			1.2	V
Current Gain Bandwidth Product	f_T	$V_{CE}=10V$ $I_C=0.5A$	10			MHz
Turn-Off Time	t_{off}	$I_C=5.0A$ $I_B=0.5A$			0.75	μS



T0-220

单位: 





BR

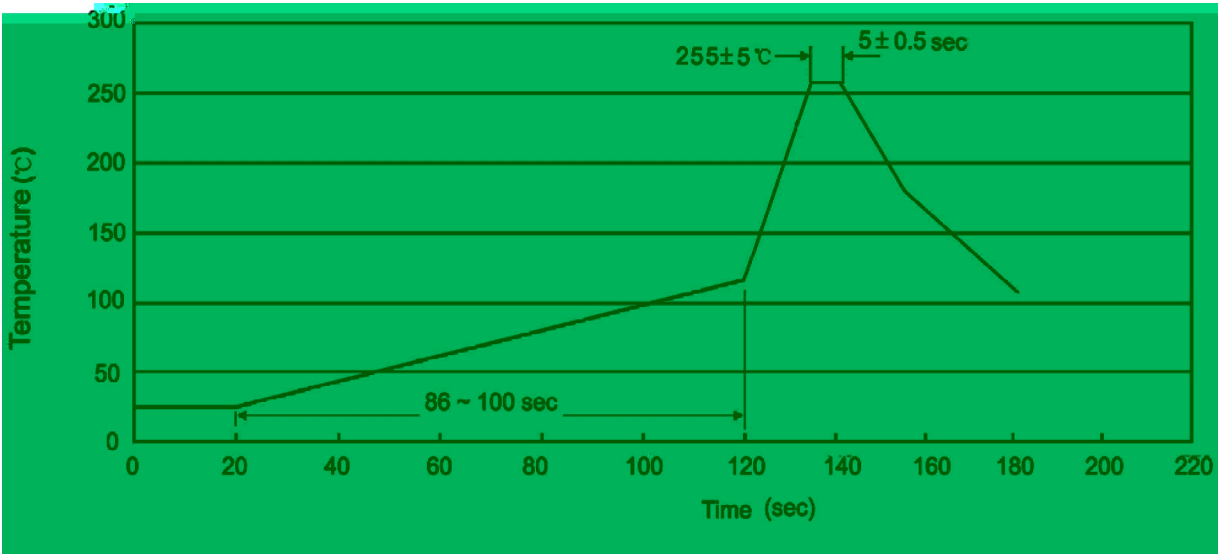
BU406

Note:

BR: Company Code

BU406: Product Type.

***: Lot No. Code, code change with Lot No.



Note:

- 1

25 150

60 90sec;
- 2

255 5

5 0.5sec;
- 3

2 10

/sec.
- 1.Preheating:25~150

, Time:60~90sec.
- 2.Peak Temp.:255 5

, Duration:5 0.5sec.
3. Cooling Speed: 2~10

/sec.

270 5

10 1 sec.

Temp.:270±5

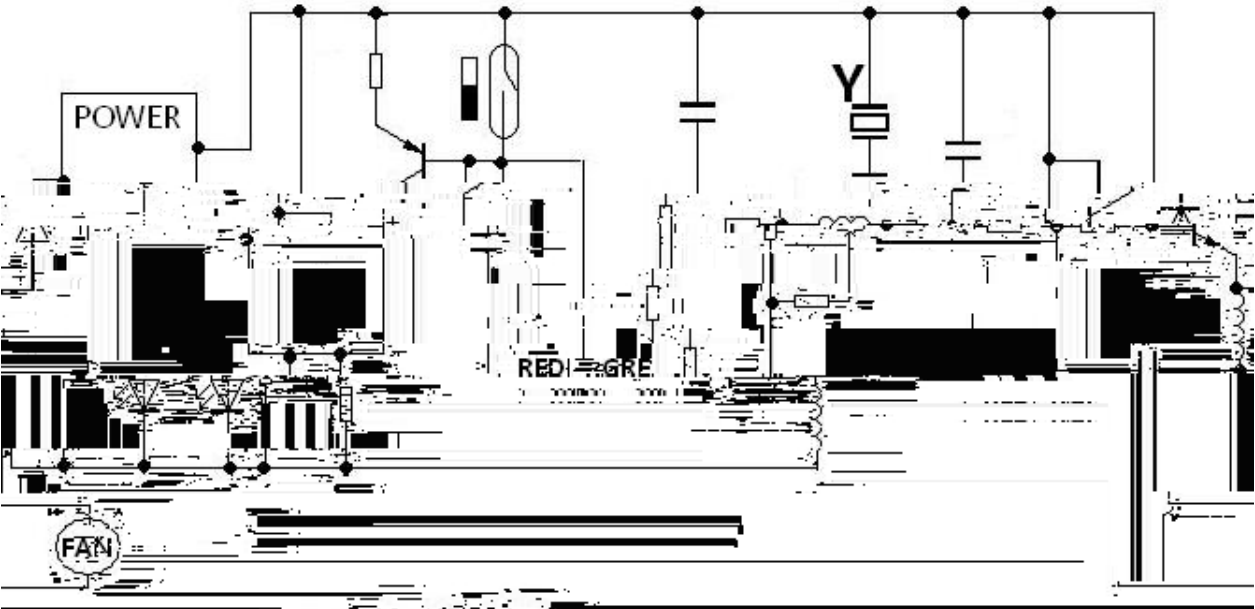
Time:10±1 sec

/ BULK

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm ³)		
	只 袋	袋 盒	只 盒	盒 箱	只 箱	袋	盒	箱

/ TUBE

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm ³)		
	只 套管	套管 盒	只 盒	盒 箱	只 箱	套管	盒	箱



加湿器原理图